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DATE	12/01/2014	HEURE	14h00
OBJET	LE PEUPLE, LE PAYS, L'ÉPOQUE, LE DÉPENSEMENT, L'AM. TOB.		
Version	1.0	Page	1

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- Failed
 - (silicon adj dioxide) SiO "SiO.sub.2")
- Saved
 - S2: (1) 09/948877
 - S3: (1736) "KONINKLIJKE PHILIPS".as.
 - S1: (0) 10/753914
 - S4: (2) "6750066".PN.
 - S5: (0) 10/775908
 - S6: (730) NROM
 - S7: (282581) (silicon adj dioxide SiO "SiO.sub.2")
 - S8: (100381) (dielectric adj constant relative adj (permittivit\$3 permittiv
 - S9: (98333) (dielectric adj constant relative adj (permittivit\$3 permittiv\$
 - S10: (4348) high adj k
 - S11: (25178) high near S9
 - S12: (28017) S10 S11

	U	Inventor	Document Issue P	Title	Current	Current X Retrieval S C P	S C P	S C P	S C P	S C P	S C P	Image Doc P	
1		Lei, Tan Fu	US 200401:2004 :9	Process of utilizing CF4 plasma pretre	438/28	438/591:	P	F	F	P	F	F	US 20040
2		Paranjpe, A U S	200300:2003 :1	Atomic layer deposition for fabricating	438/14	257/E21.2	P	F	F	P	F	F	US 20030
3		Min, Yo Se	US 666999:2003 :1	Atomic layer deposition method using	427/25	427/255.3	P	F	F	P	F	F	US 66699
4		Rausch, W	US 200402:2004 :1	Method of forming precision recessed	438/19	438/482:	P	F	F	P	F	F	US 20040
5		Aoyama, S	US 200402:2004 :5	Method and device for processing sub	438/88		P	F	F	P	F	F	US 20040
6		Conley, Jo	US 200402:2004 :1	Modulated temperature method of ato	438/77	438/782	P	F	F	P	F	F	US 20040
7		Yeo, Yee-C	US 200401:2004 :1	Semiconductor chip with gate dielectri	257/50		P	F	F	P	F	F	US 20040
8		Bude, Jeffr	US 200401:2004 :3	Semiconductor devices with reduced	438/93	257/431:	P	F	F	P	F	F	US 20040
9		Jang, Chuc	US 200400:2004 :1	Atomic layer deposition of interpoly oxl	257/31	257/E21.2	P	F	F	P	F	F	US 20040
10		Lee, Yun-J	US 200400:2004 :2	Method of forming oxide layer using at	438/75	257/E21.2	P	F	F	P	F	F	US 20040